Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H9015

APPLICATIONS

LOW FREQUENCY, LOW NOISE AMPLIFIER

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····450mW

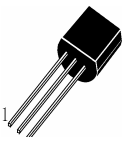
V_{CBO}——Collector-Base Voltage·····-50V

V_{CEO}——Collector-Emitter Voltage·····-45V

V_{EBO}——Emitter-Base Voltage·····-5V

I_C——Collector Current·····-100mA

TO-92



1—Emitter, E
2—Base, B
3—Collector, C

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-0.05	μA	V_{CB}=-30V, I_E=0
I_{EBO}	Emitter Cut-off Current			-0.05	μA	V_{EB}=-5V, I_C=0
$H_{FE(1)}$	DC Current Gain	60		800		V_{CE}=-5V, I_C=-1mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.7	V	I_C=-100mA, I_B=-5mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			-1.0	V	I_C=-100mA, I_B=-5mA
BV_{CBO}	Collector-Base Breakdown Voltage	-50			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-45			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-100μA, I_C=0
Cob	Output Capacitance		4.5	7.0	pF	V_{CB}=-10V, I_E=0, f=1MHz
f_T	Current Gain-Bandwidth Product	100			MHz	V_{CE}=-5V, I_C=-10mA

h_{FE} Classification

A	B	C	D
60—150	100—300	200—600	400—800

Typical Characteristics

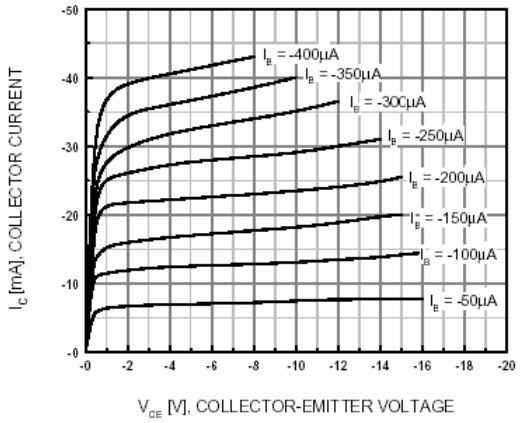


Figure 1. Static Characteristic

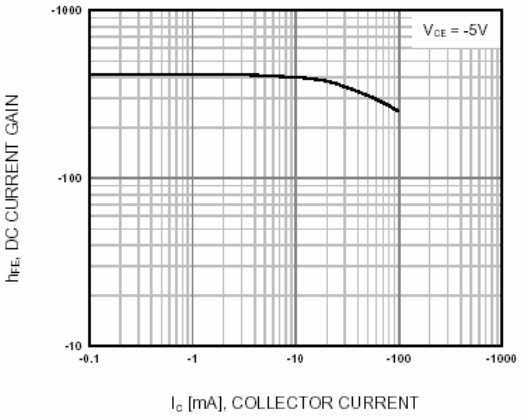


Figure 2. DC current Gain

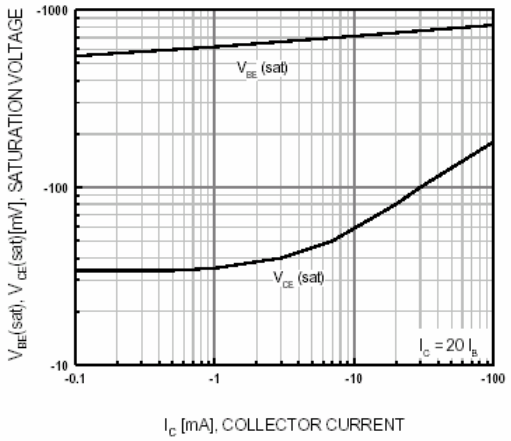


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

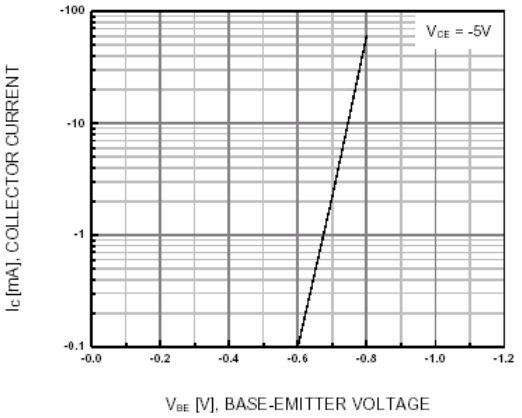


Figure 4. Base-Emitter On Voltage

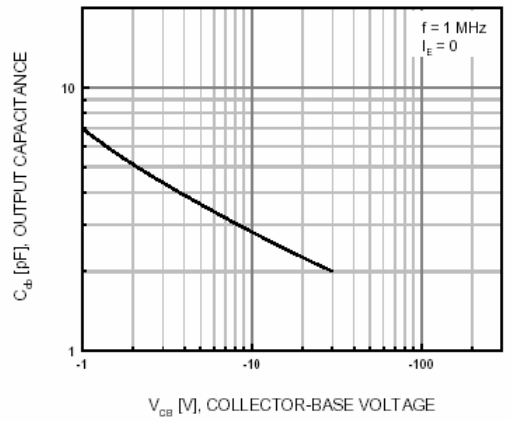


Figure 5. Collector Output Capacitance

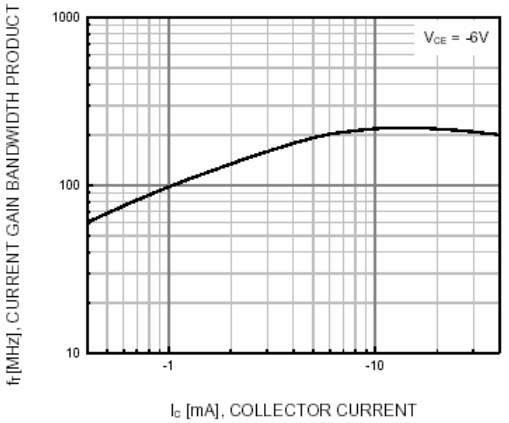


Figure 6. Current Gian Bandwidth Product